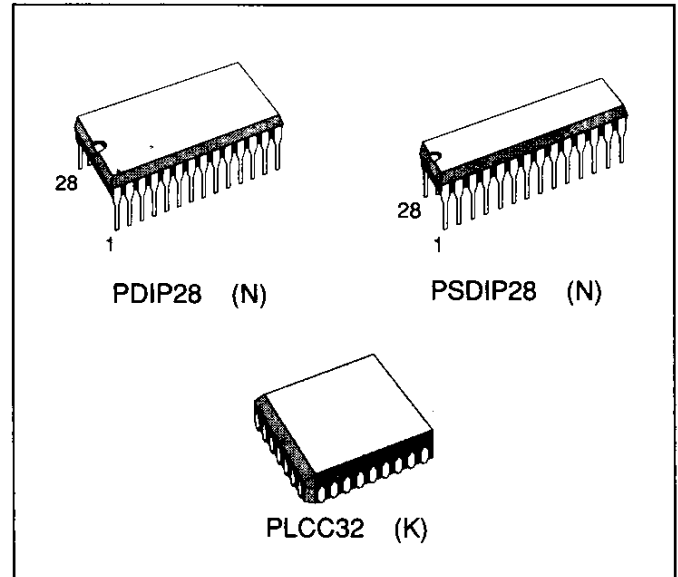


## VERY FAST CMOS 512 / 1K / 2K x 9 BiPORT FIFO

- FIRST-IN-FIRST-OUT MEMORY BASED ARCHITECTURE
- FLEXIBLE x 9 ORGANIZATIONS:
  - MK45H01,11 (512 x 9)
  - MK45H02,12 (1K x 9)
  - MK45H03,13 (2K x 9)
- LOW POWER, HIGH SPEED HCMOS TECHNOLOGY
- ASYNCHRONOUS AND SIMULTANEOUS READ/WRITE
- FULLY EXPANDABLE IN WORD WIDTH AND DEPTH
- EMPTY AND FULL WARNING FLAGS
- RETRANSMIT CAPABILITY
- HALF-FULL FLAG IN SINGLE DEVICE MODE



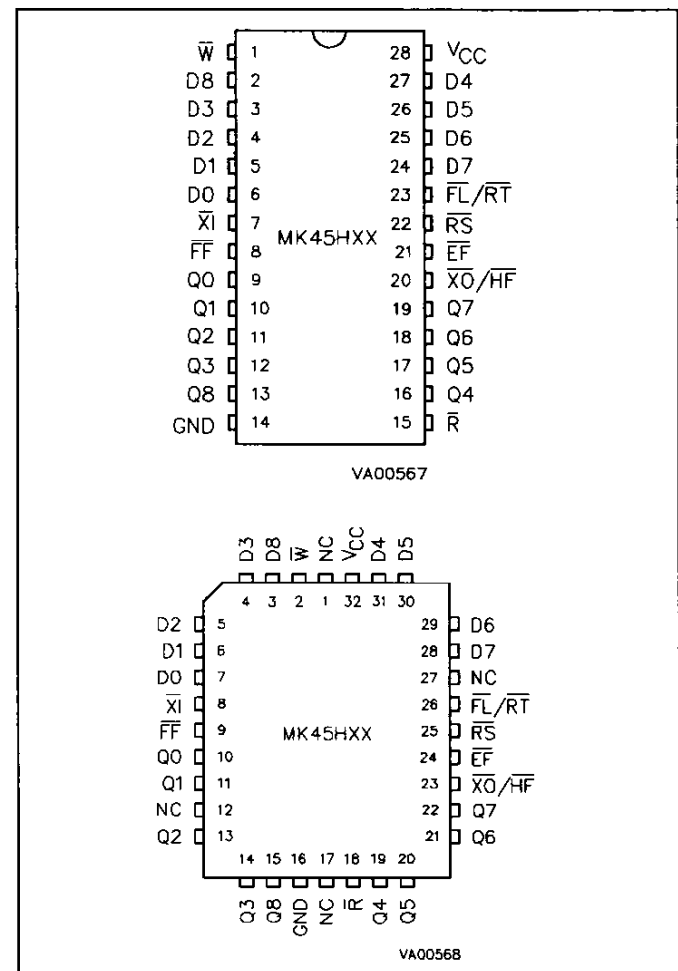
### DESCRIPTION

The MK45H01,11,02,12,03,13 are BiPORT™ FIFO memories from SGS-THOMSON Microelectronics, which utilize special two-port memory cell techniques. Specifically, these devices implement a First-In-First-Out (FIFO) algorithm, featuring asynchronous read/write operations, full, empty, and half full status flags, and unlimited expansion capability in both word size and depth. The full and empty flags are provided to prevent data overflow and underflow.

### PIN NAMES

$\bar{W}$	Write
$\bar{R}$	Read
$\bar{RS}$	Reset
D0-D8	Data Inputs
Q0-Q8	Data Outputs
$\bar{FL}/\bar{RT}$	First Load / Retransmit
$\bar{XI}$	Expansion Input
$\bar{XO}/\bar{HF}$	Expansion Output / Half-full Flag
$\bar{FF}$	Full Flag
$\bar{EF}$	Empty Flag
V <sub>CC</sub> , GND	5 Volts, Ground
NC	Not Connected

Figure 1. Pin Connections





## FUNCTIONAL DESCRIPTION (Continued)

As long as the pointers do not catch one another, the FIFO can be written and read continuously without ever becoming full or empty.

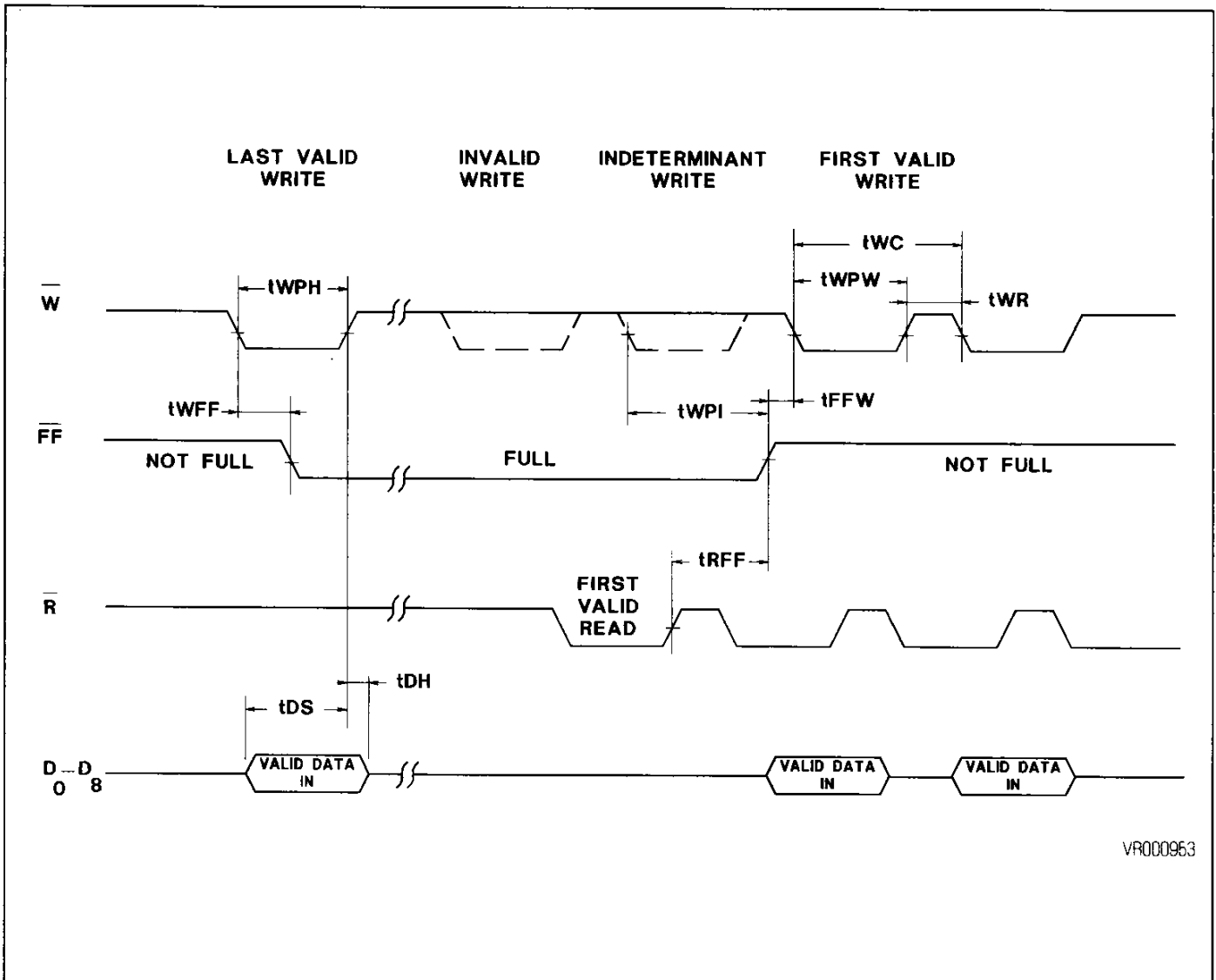
Resetting the FIFO simply resets the write and read pointers to location zero. Pulsing retransmit resets the read address pointer without effecting the write address pointer.

With conventional FIFOs, implementation of a larger FIFO is accomplished by cascading individual FIFOs. The penalty of cascading is often unacceptable ripple through delays. The MK45HX1, MK45HX2, and MK45HX3 allow implementation of very large FIFOs with no timing penalties. The memory-based architecture of the device allows the connection of the read, write, data in, and data out lines of the device in parallel. The write and read control circuits of the individual FIFOs are then automatically enabled and disabled through the expansion-in and expansion-out pins.

## WRITE MODE

The MK45HXX initiates a Write Cycle (see Figure 3) on the falling edge of the Write Enable control input ( $\bar{W}$ ), provided that the Full Flag ( $\bar{FF}$ ) is not set. Data set-up and hold-time requirements must be satisfied with respect to the rising edge of  $\bar{W}$ . The data is stored sequentially and independent of any ongoing Read operations.  $\bar{FF}$  is set during the last valid write as the MK45H03 becomes full. Write operations begun with  $\bar{FF}$  low are inhibited.  $\bar{FF}$  will go high  $t_{RFF}$  after completion of a valid READ operation.  $\bar{FF}$  will again go low  $t_{WFF}$  from the beginning of a subsequent WRITE operation, provided that a second READ has not been completed (see Figure 5). Writes beginning  $t_{FFW}$  after  $\bar{FF}$  goes high are valid. Writes beginning after  $\bar{FF}$  goes low and more than  $t_{WPI}$  before  $\bar{FF}$  goes high are invalid (ignored). Writes beginning less than  $t_{WPI}$  before  $\bar{FF}$  goes high and less than  $t_{FFW}$  later may or may not occur (be valid), depending on the internal flag status.

Figure 3. Write and Full Flag Waveforms



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**Write and Full Flag AC Operating Conditions**  
 (0°C ≤ T<sub>A</sub> ≤ +70°C, V<sub>CC</sub> = +5V ± 10%)

Symbol	Parameter	-25		-35		-50		-65		-12		Unit	Note
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
t <sub>WC</sub>	Write Cycle Time	35		45		65		80		140		ns	
t <sub>WPW</sub>	Write Pulse Width	25		35		50		65		120		ns	1
t <sub>WR</sub>	Write Recovery Time	10		10		15		15		20		ns	
t <sub>DS</sub>	Data Set Up Time	15		18		30		30		40		ns	
t <sub>DH</sub>	Data Hold Time	0		0		0		0		0		ns	
t <sub>WFF</sub>	$\bar{W}$ Low to $\bar{FF}$ Low		25		35		45		60		60	ns	2
t <sub>FFW</sub>	$\bar{FF}$ High to Valid Write		10		10		10		10		10	ns	2
t <sub>RFF</sub>	$\bar{R}$ High to $\bar{FF}$ High		25		35		45		60		60	ns	2
t <sub>WPI</sub>	Write Protect Indeterminant	10		10		10		10		10		ns	2

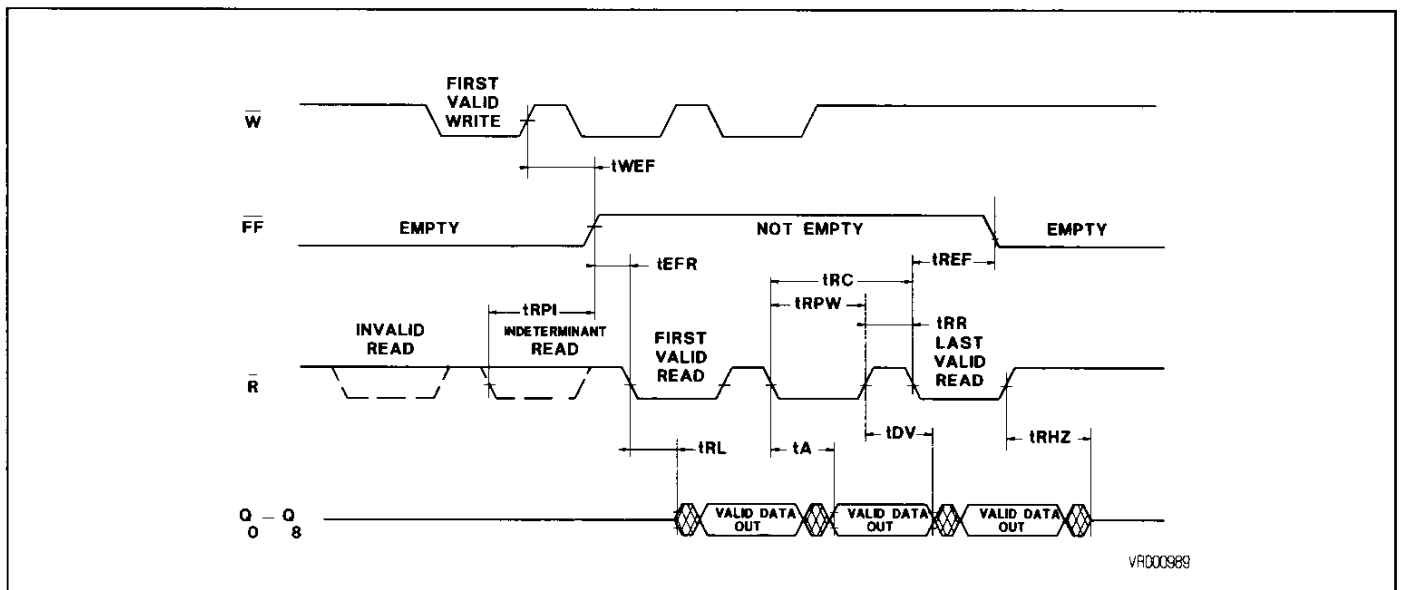
**Notes:** 1. Pulse widths less than minimum values are not allowed  
 2. Measured using equivalent output load circuit

**READ MODE**

The MK45HXX initiates a Read Cycle (see Figure 4) on the falling edge of Read Enable control input ( $\bar{R}$ ), provided that the Empty Flag ( $\bar{EF}$ ) is not set. In the read mode of operation, the MK45H0X provides fast access to data from 9 of the locations in the static storage array. The data is accessed on a FIFO basis independent of any on-going WRITE operations. After  $\bar{R}$  goes high, data outputs will return to a high impedance condition until the next read operation. In the event that all data has been read from the FIFO, the  $\bar{EF}$  will go low, and further

READ operations will be inhibited (the data inputs will remain in high impedance).  $\bar{EF}$  will go high t<sub>WEF</sub> after completion of a valid WRITE operation.  $\bar{EF}$  will again go low t<sub>REF</sub> from the beginning a subsequent read operation, provided that a second WRITE has not been completed (see Figure 6). Reads beginning t<sub>EFR</sub> after  $\bar{EF}$  goes high are valid. Reads begun after  $\bar{EF}$  goes low and more than t<sub>RPI</sub> before  $\bar{EF}$  goes high are invalid (ignored). Reads beginning less than t<sub>RPI</sub> before  $\bar{EF}$  goes high and less than t<sub>EFR</sub> later may or may not occur (be valid) depending on internal flag status.

**Figure 4. Read and Empty Flag Waveforms**

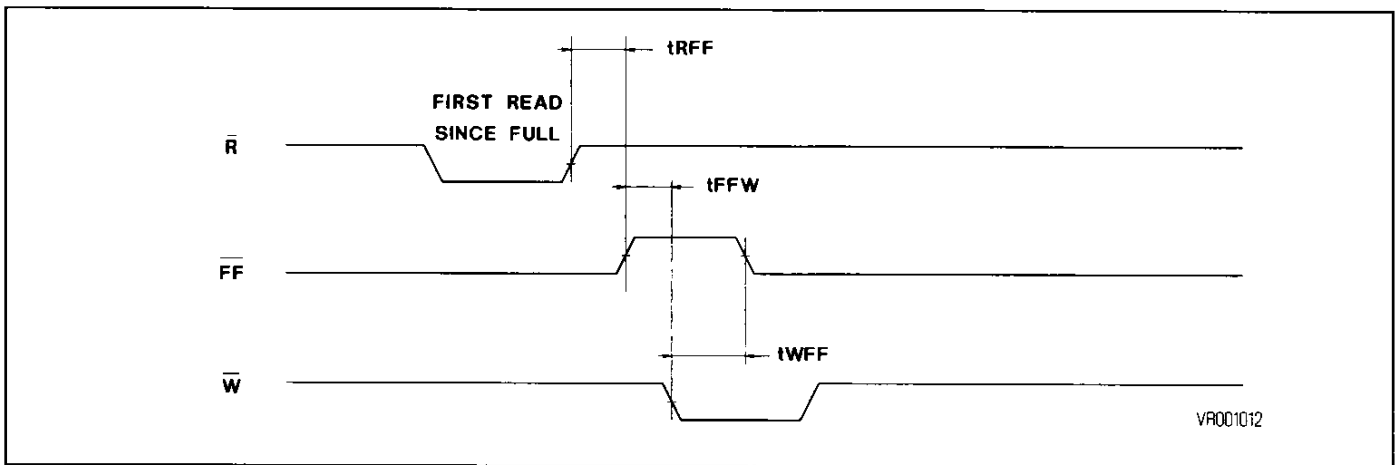


**Read and Empty Flag AC Operating Conditions**  
 (0°C ≤ T<sub>A</sub> ≤ +70°C, V<sub>CC</sub> = +5V ± 10%)

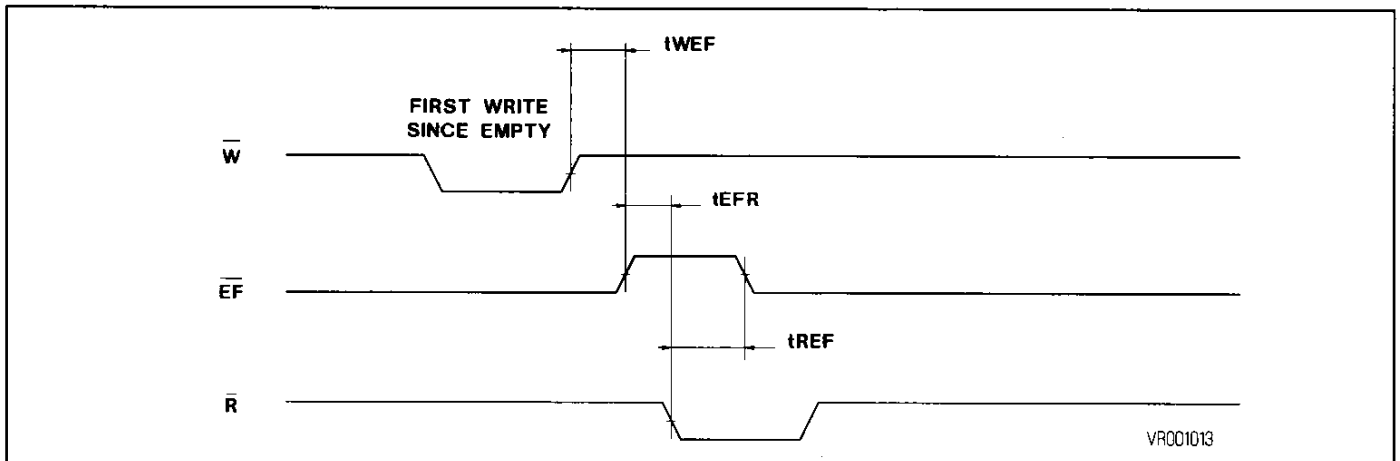
Symbol	Parameter	-25		-35		-50		-65		-12		Unit	Note
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
t <sub>RC</sub>	Read Cycle Time	35		45		65		80		140		ns	
t <sub>A</sub>	Access Time		25		35		50		65		120	ns	2
t <sub>RR</sub>	Read Recovery Time	10		10		15		15		20		ns	
t <sub>RPW</sub>	Read Pulse Width	25		35		50		65		120		ns	1
t <sub>RL</sub>	$\bar{R}$ Low to Low Z	0		0		0		0		0		ns	2
t <sub>DV</sub>	Data Valid from $\bar{R}$ High	5		5		5		5		5		ns	2
t <sub>RHZ</sub>	$\bar{R}$ High to High Z		18		20		25		25		35	ns	2
t <sub>REF</sub>	$\bar{R}$ Low to $\bar{EF}$ Low		25		35		40		60		60	ns	2
t <sub>EFR</sub>	$\bar{EF}$ High to Valid Read		10		10		10		10		10	ns	2
t <sub>WEF</sub>	$\bar{W}$ High to $\bar{EF}$ High		25		35		45		60		60	ns	2
t <sub>RPI</sub>	Read Protect Indeterminant	10		10		10		10		10		ns	2

Notes: 1. Pulse widths less than minimum values are not allowed  
 2. Measured using equivalent output load circuit

**Figure 5. Read/Write to Full Flag Waveforms**



**Figure 6. Write/Read to Empty Flag Waveforms**

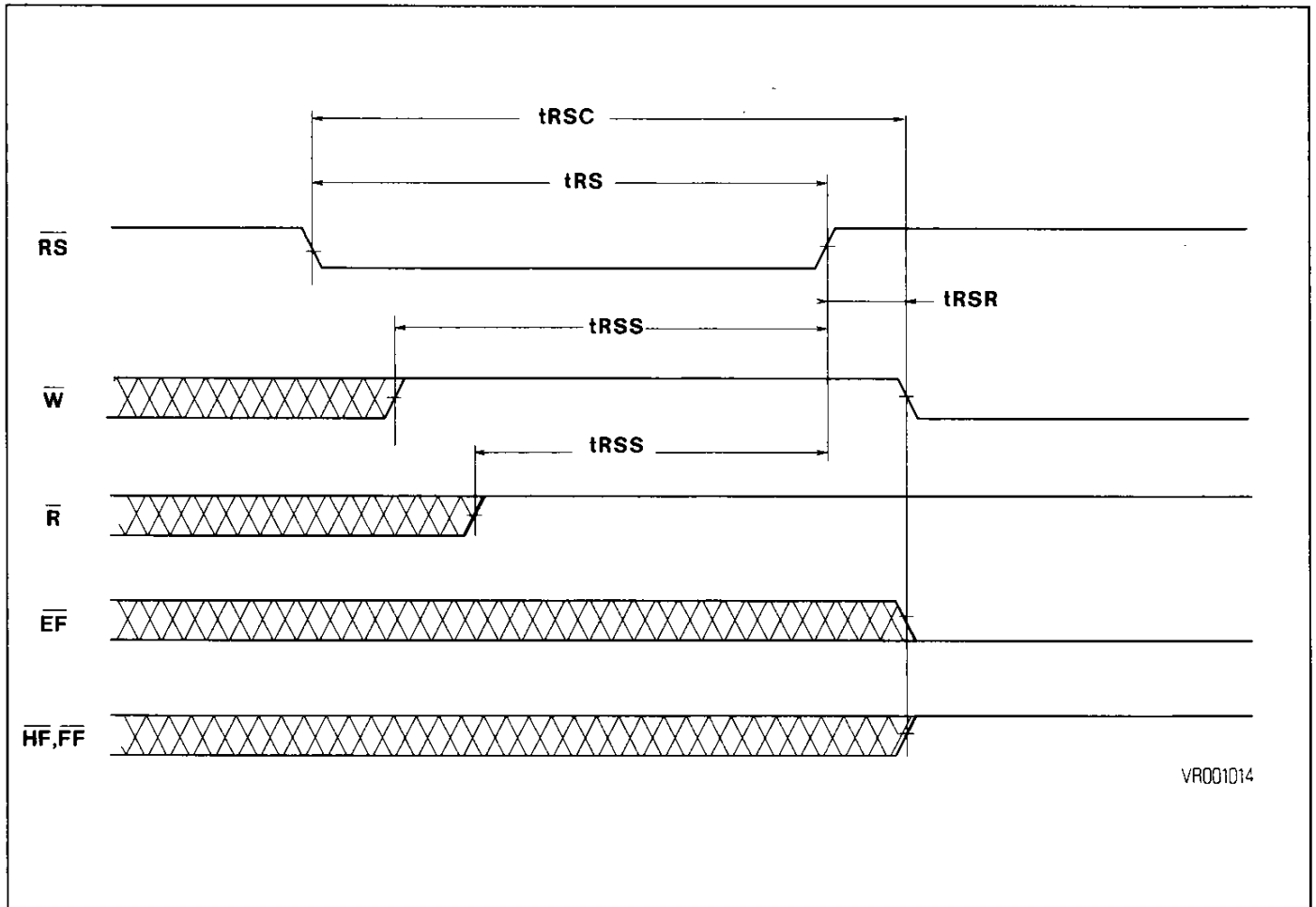


**RESET**

The MK45HXX is reset (see Figure 7) whenever the Reset pin ( $\overline{RS}$ ) is in the low state. During a reset, both the internal read and write pointers are set to the first location. Reset is required after power up, before a WRITE operation can begin.

Although neither  $\overline{W}$  or  $\overline{R}$  need be high when  $\overline{RS}$  goes low, both  $\overline{R}$  and  $\overline{W}$  must be high  $t_{RSS}$  before  $\overline{RS}$  goes high, and must remain high  $t_{RSR}$  afterwards. Refer to the following discussion for the required state of  $\overline{FL/RT}$  and  $\overline{XI}$  during Reset.

**Figure 7. Reset Waveforms**



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Note :  $\overline{HF}$ ,  $\overline{EF}$  and  $\overline{FF}$  may change status during Reset, but flags will be valid at  $t_{RSC}$ .

**Reset AC Operating Conditions** ( $0^{\circ}\text{C} \leq T_A \leq +70^{\circ}\text{C}$ ,  $V_{CC} = +5\text{V} \pm 10\%$ )

Symbol	Parameter	-25		-35		-50		-65		-12		Unit	Note
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
$t_{RSC}$	Reset Cycle Time	35		45		65		80		140		ns	
$t_{RS}$	Reset Pulse Width	25		35		50		65		120		ns	1
$t_{RSR}$	Reset Recovery Time	10		10		15		15		20		ns	
$t_{RSS}$	Reset Set Up Time	25		30		30		45		100		ns	

Note: 1. Pulse widths less than minimum values are not allowed



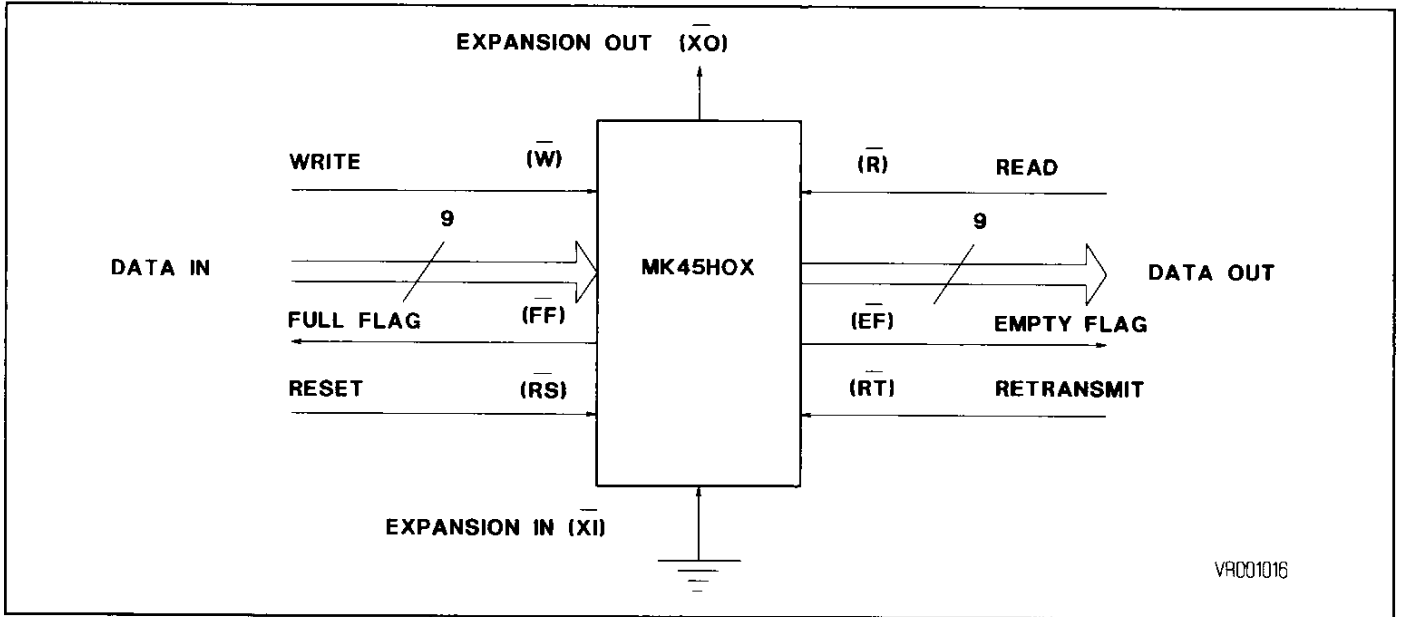
**SINGLE DEVICE CONFIGURATION**

A single MK45HXX may be used when application requirements are for a depth of the device depth or less. The MK45HXX is placed in the Single Device Configuration mode when the chip is Reset with the Expansion In pin ( $\bar{X}I$ ) grounded (see Figure 9).

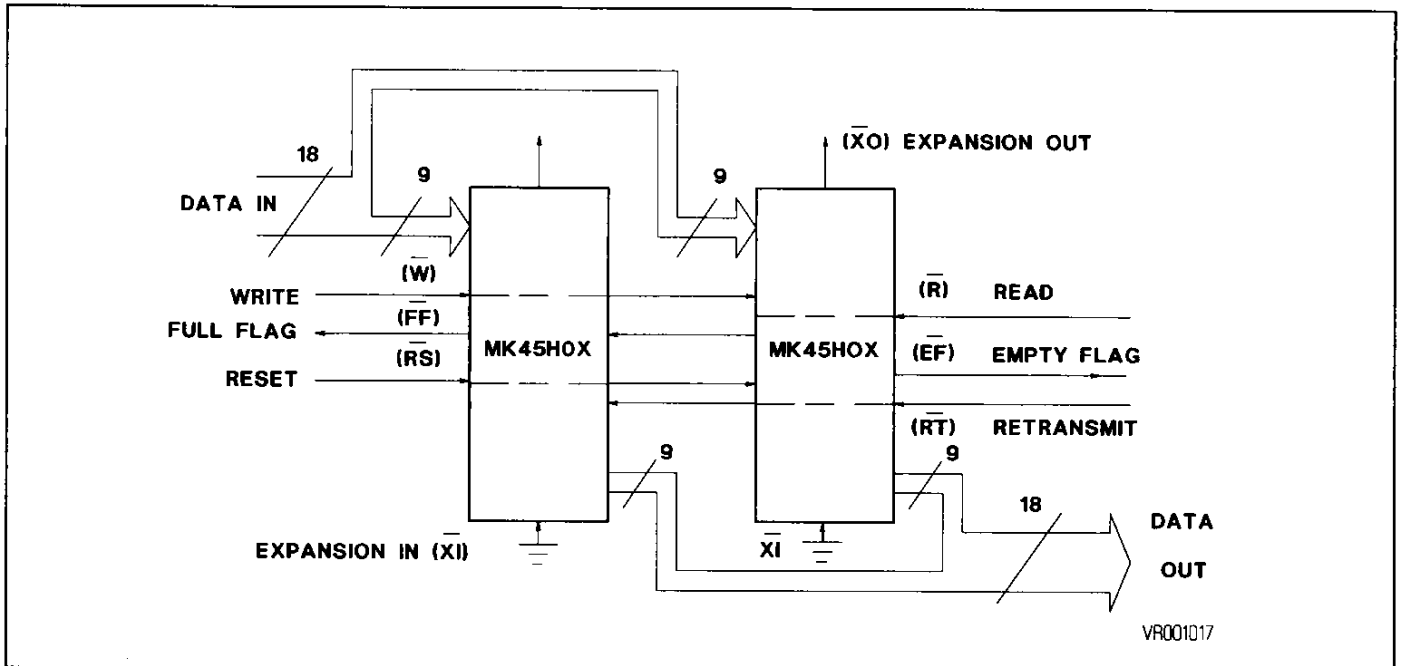
**WIDTH EXPANSION**

Word width may be increased simply by connecting the corresponding input control signals of multiple devices. Status Flags ( $\bar{E}F$  and  $\bar{F}F$ ) can be detected from any one device. Figure 10 demonstrates an 18-bit word width by using two MK45HXXs. Any word width can be attained by adding additional MK45HXXs. The half full flag ( $\bar{H}F$ ) operates the same as in single device configuration.

**Figure 9. A Single MK45HXX FIFO Configuration**



**Figure 10. A Two Device Width Expansion FIFO Configuration**



**Note :** Flag detection is accomplished by monitoring the FF and EF signals on either (any) device used in the width expansion configuration. Do not connect flag output signals together.



## HALF FULL FLAG LOGIC

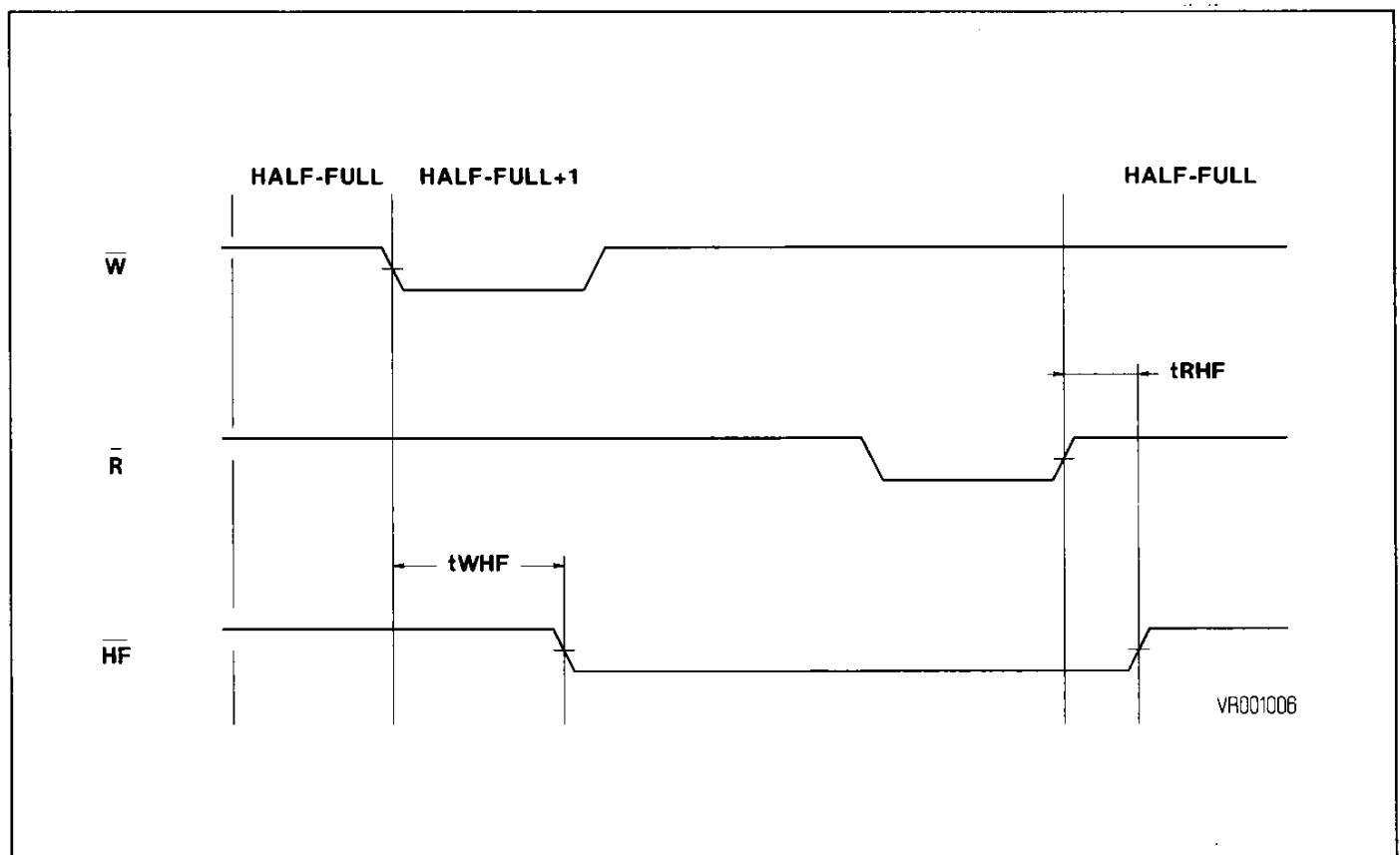
When in single device configuration, the ( $\overline{\text{HF}}$ ) output acts as an indication of a half full memory. After half of the memory is filled, and at the falling edge of the next write operation, the half full flag ( $\overline{\text{HF}}$ ) will be set low and remain low until the difference between the write pointer and read pointer is less than or equal to one half the total memory. The half full flag ( $\overline{\text{HF}}$ ) is then reset by the rising edge of the read operation (see Figure 11).

## DEPTH EXPANSION (Daisy Chain)

The MK45HXX can be easily adapted to applications when the requirements are greater than the individual device word depth. Figure 12 demonstrates Depth Expansion using two MK45HXXs. Any depth can be attained by adding additional MK45HXXs.

External logic is needed to generate a composite Full and Empty Flag. This requires the ORing of all the EFs and the ORing of all the FFs (i.e., all must be set to generate the composite FF or EF).

Figure 11. Half Full Flag Waveforms



## Half Full Flag AC Operating Conditions

( $0^{\circ}\text{C} \leq T_A \leq +70^{\circ}\text{C}$ ,  $V_{\text{CC}} = +5\text{V} \pm 10\%$ )

Symbol	Parameter	-25		-35		-50		-65		-12		Unit	Note
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
$t_{\text{WHF}}$	Write Low to Half Full Flag Low		30		35		45		60		60	ns	
$t_{\text{RHF}}$	Read High to Half Full Flag High		30		35		45		60		60	ns	

The MK45HXX operates in the Depth Expansion configuration after the chip is Reset under the below listed conditions :

1. The first device must be designated by grounding the First Load pin ( $\overline{FL}$ ). The Retransmit function is not available in the Depth Expansion Mode.
2. All other devices must have  $\overline{FL}$  in the high state.
3. The Expansion Out ( $\overline{XO}$ ) pin of each device must be tied to the Expansion In ( $\overline{XI}$ ) pin of the next device. The Half Full Flag ( $\overline{HF}$ ) is disabled in this mode.

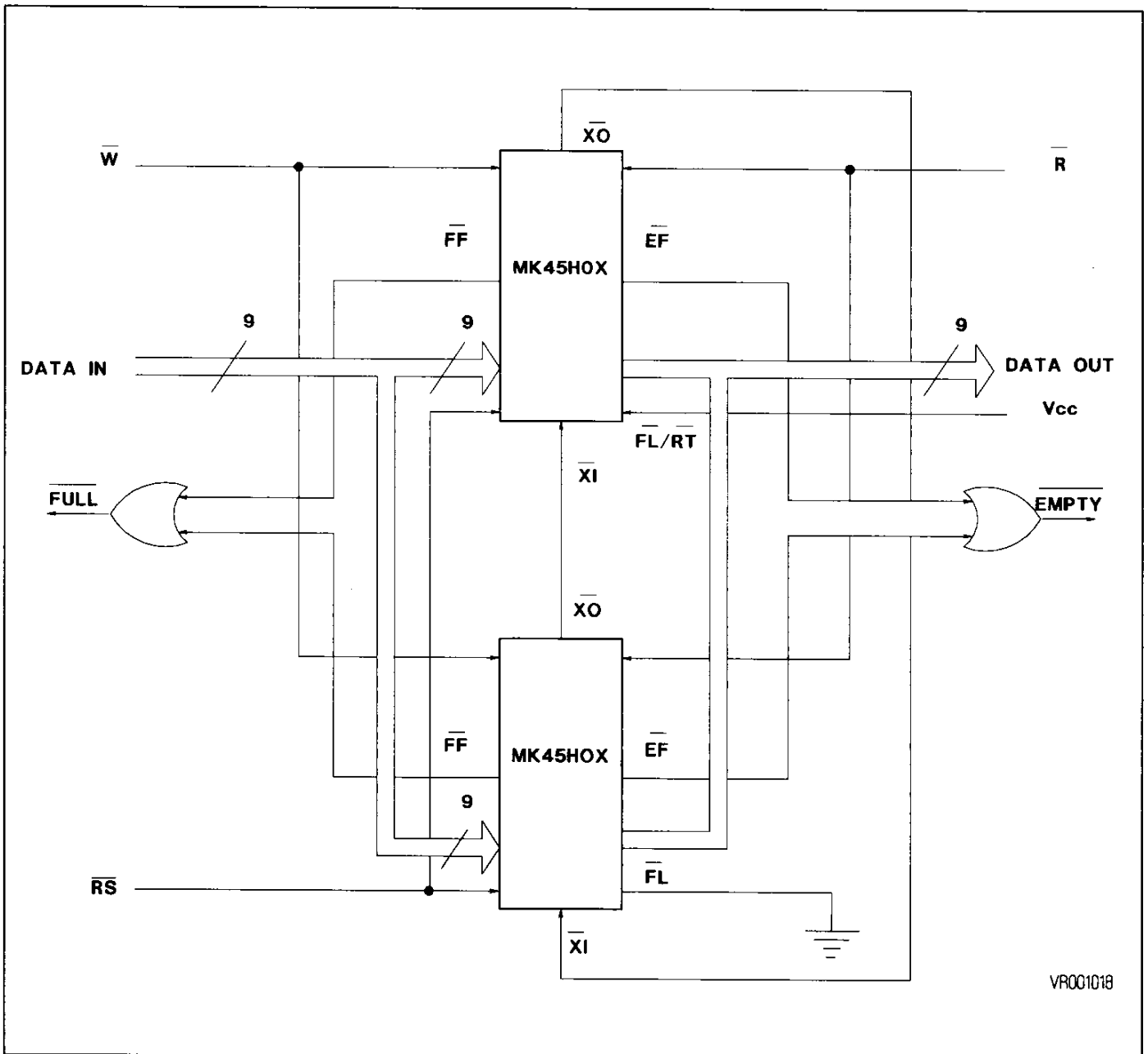
Expansion Out and Expansion In signals. Discussion of Expansion Out/Expansion In timing is provided to clarify how Depth Expansion works. Due to the fact that Expansion Out pins are generally connected only to Expansion In pins, the user does not need to be concerned with the actual timing in a normal Depth Expanded application unless extreme propagation delays exist between the  $\overline{XO}/\overline{XI}$  pin pairs.

Expansion Out pulses are the identical to the WRITE and READ signals but ; delayed in time by  $t_{XOL}$  and  $t_{XOH}$ . The Expansion Out signal is propagated when the last physical location in the memory array is written and again when it is read (Last Read). This is in contrast to when the Full and Empty Flags are activated, which is in response to writing and reading a last available location.

**EXPANSION TIMING**

Figures 13 and 14 illustrate the timing of the Ex-

**Figure 12. A Two Device Depth Expansion Configuration**

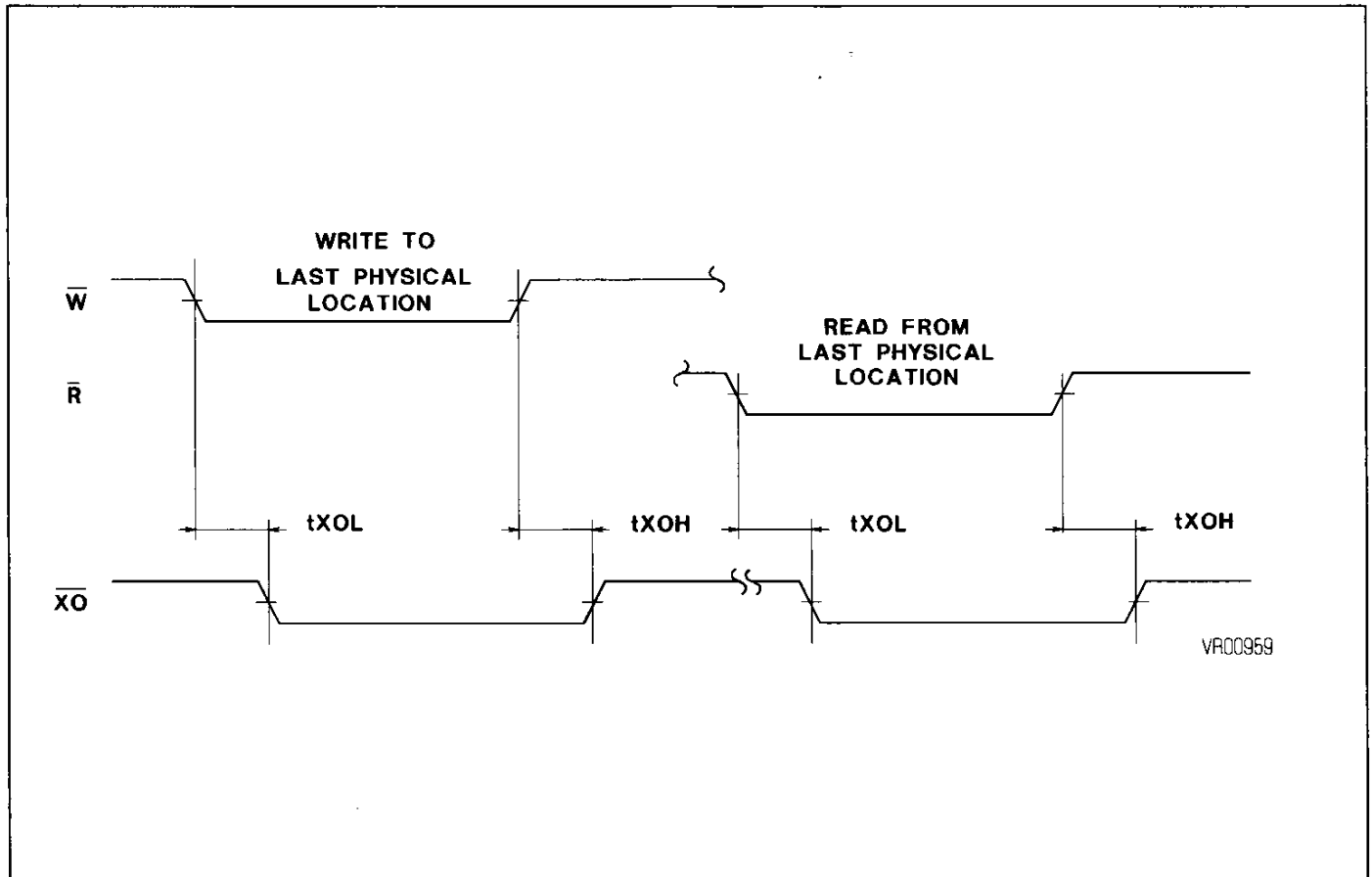


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When in Depth Expansion mode, a given MK45HXX will begin writing and reading as soon as valid WRITE and READ signals begin, provided FL was grounded at RESET time. A MK45HXX in Depth Expansion mode with FL high at RESET will not begin writing until after an Expansion In pulse occurs.

It will not begin reading until a second Expansion In pulse and the Empty Flag has gone high. Expansion In pulses must occur  $t_{XIS}$  before the WRITE and READ signals are intended to enable. Minimum Expansion In pulse width,  $t_{XI}$ , and recovery time,  $t_{XIR}$ , must be observed.

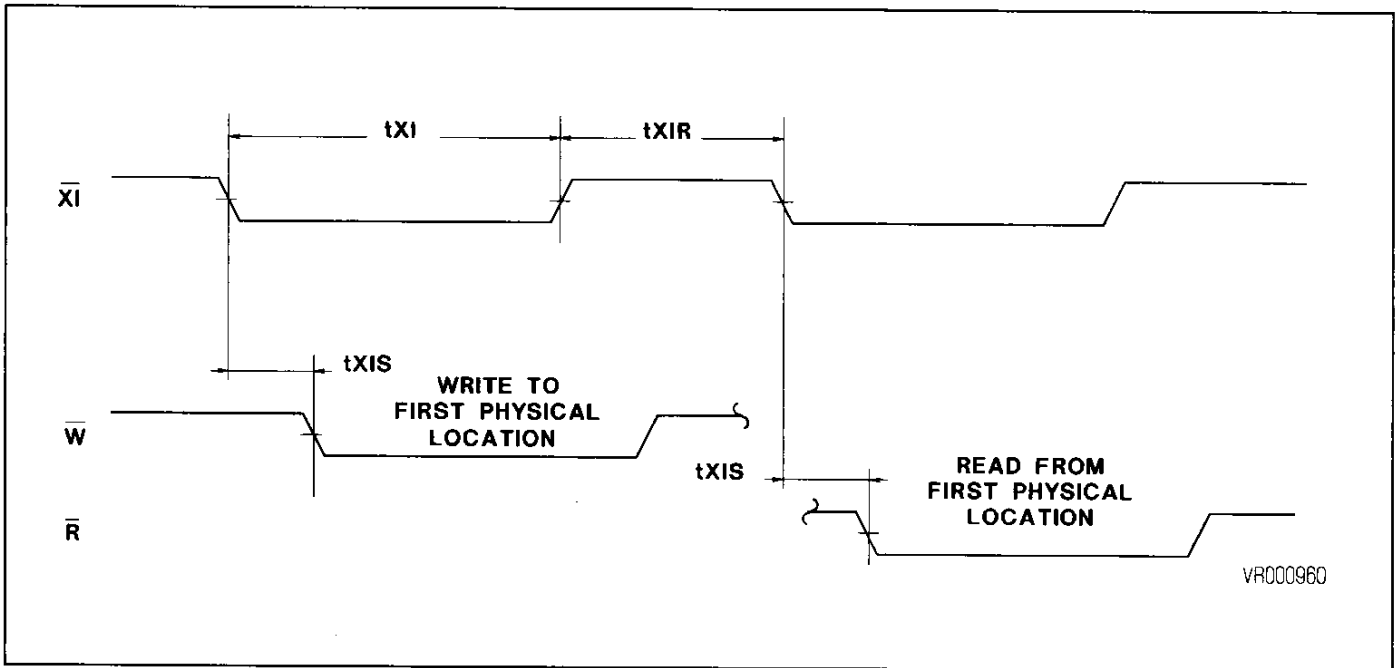
Figure 13. Expansion Out Waveforms



**Expansion Out AC Operating Conditions**  
 ( $0^{\circ}\text{C} \leq T_A \leq +70^{\circ}\text{C}$ ,  $V_{CC} = +5\text{V} \pm 10\%$ )

Symbol	Parameter	-25		-35		-50		-65		-12		Unit	Note
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
$t_{XOL}$	Expansion Out Low		25		35		40		55		90	ns	
$t_{XOH}$	Expansion Out High		25		35		40		55		90	ns	

Figure 14. Expansion In Waveforms



**Expansion In AC Operating Conditions**  
 (0°C ≤ TA ≤ +70°C, VCC = +5V ± 10%)

Symbol	Parameter	-25		-35		-50		-65		-12		Unit	Note
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
txi	Expansion in Pulse Width	25		35		45		60		115		ns	1
txir	Expansion In Recovery Time	10		10		10		10		10		ns	
txis	Expansion In Setup Time	15		15		15		15		15		ns	

**Note:** 1. Pulse widths less than minimum values are not allowed

**COMPOUND EXPANSION**

The two expansion techniques described above can be applied together in a straight forward manner to achieve large FIFO arrays (see Figure 15).

**BIDIRECTIONAL APPLICATIONS**

Applications, which require data buffering between

two systems (each system capable of READ and WRITE operations), can be achieved by pairing MK45HXXs, as shown in Figure 16. Care must be taken to ensure that the appropriate flag is monitored by each system. (i.e., FF is monitored on the device where W is used ; EF is monitored on the device where R is used). Both Depth Expansion and Width Expansion may be used in this mode.

Figure 15. Compound FIFO Expansion Configuration

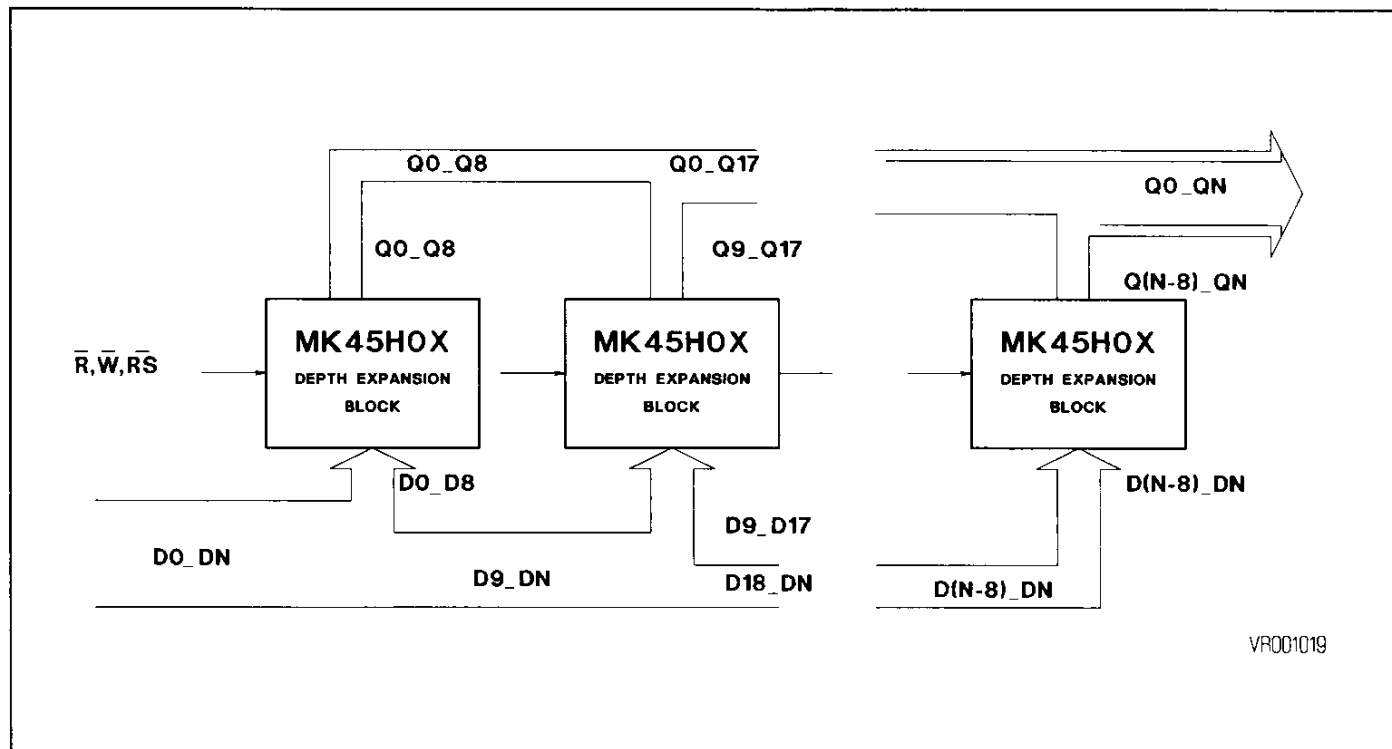
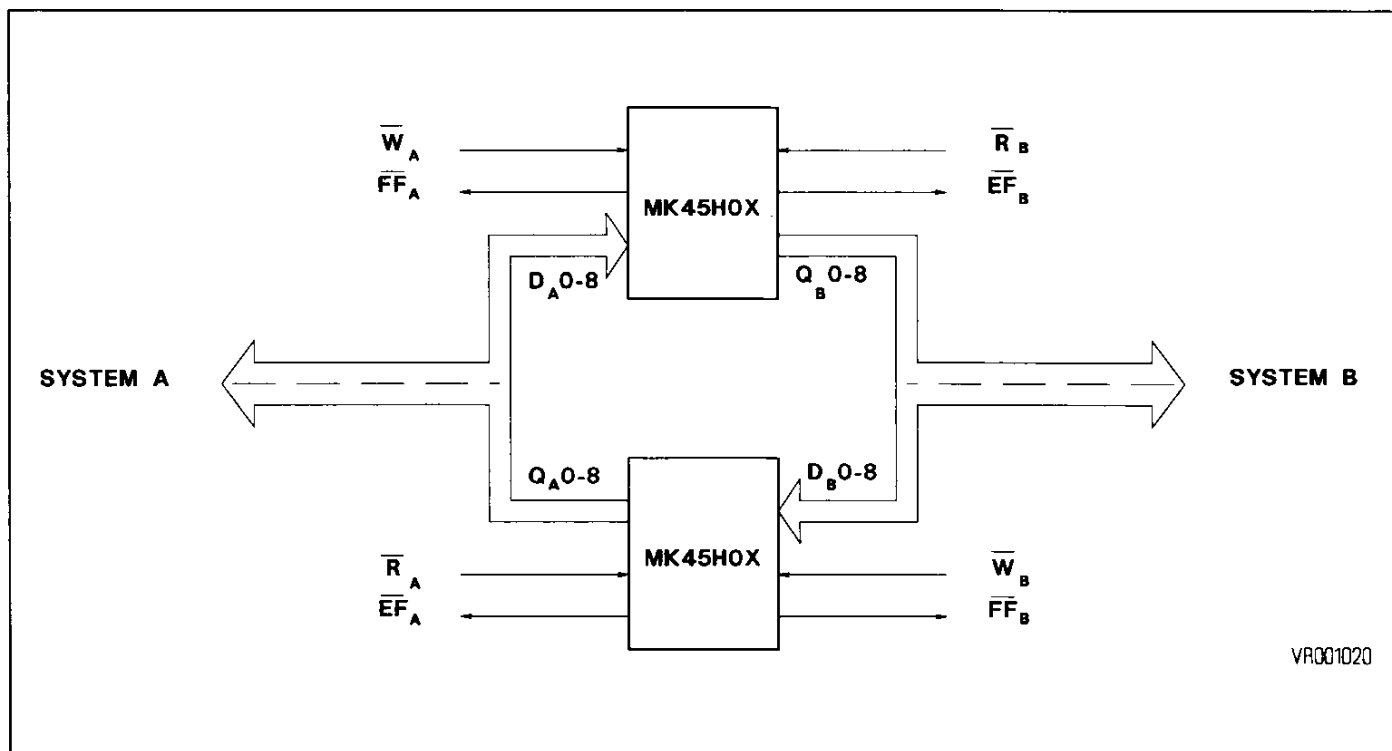


Figure 16. Bidirectional FIFO Application



**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>I</sub>	Voltage on any Pin Relative to Ground	-0.3 to +7	V
T <sub>A</sub>	Operating Temperature	0 to 70	°C
T <sub>STG</sub>	Storage Temperature	-55 to +125	°C
P <sub>D</sub>	Power Dissipation	1	W
I <sub>OUT</sub>	Output Current	20	mA

**Note :** This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operation sections of this specification is not implied. Exposure to absolute maximum ratings for extended periods of time may affect device reliability.

**RECOMMENDED DC OPERATING CONDITIONS (0°C ≤ T<sub>A</sub> ≤ +70°C)**

Symbol	Parameter	Min.	Max.	Units	Note
V <sub>CC</sub>	Supply Voltage	4.5	5.5	V	1
GND	Ground	0	0	V	
V <sub>IH</sub>	Logic 1 All Inputs	2	V <sub>CC</sub> + 0.3	V	1,2
V <sub>IL</sub>	Logic 0 All Inputs	-0.3	0.8	V	1

**Notes:** 1. All Voltages are referenced to ground  
 2. V<sub>IH</sub> = 2.5V on the RS pin for MK45H01,11, 02,12

**DC ELECTRICAL CHARACTERISTICS (0°C ≤ T<sub>A</sub> ≤ +70°C, V<sub>CC</sub> = +5V ± 10%)**

Symbol	Parameter	Min.	Max.	Units	Note
I <sub>CC1</sub>	Average V <sub>CC</sub> Power Supply Current		120	mA	1
I <sub>CC2</sub>	Average Standby Current ( $\bar{R} = \bar{W} = \bar{RS} = \bar{FL} / \bar{RT} = V_{IH}$ )		12	mA	1
I <sub>CC3</sub>	Power Down Current (Inputs ≥ V <sub>CC</sub> - 0.2V)		2	mA	1
I <sub>IL</sub>	Input Leakage Current (Any Input)	-1	1	μA	2
I <sub>OL</sub>	Output Leakage Current	-10	10	μA	3
V <sub>OH</sub>	Output Logic 1 Voltage (I <sub>OUT</sub> = -4.0mA)	2.4		V	4
V <sub>OL</sub>	Output Logic 0 Voltage (I <sub>OUT</sub> = 8.0mA)		0.4	V	4

**Notes :** 1. I<sub>CC</sub> measurements are made with outputs open.  
 2. Measured with 0.4V ≤ V<sub>IN</sub> ≤ V<sub>CC</sub>.  
 3.  $\bar{R} \geq V_{IH}$ , 0.4 ≥ V<sub>OUT</sub> ≤ V<sub>CC</sub>.  
 4. All voltages are referenced to ground.

**CAPACITANCE (T<sub>A</sub> = 25°C, f = 1MHz)**

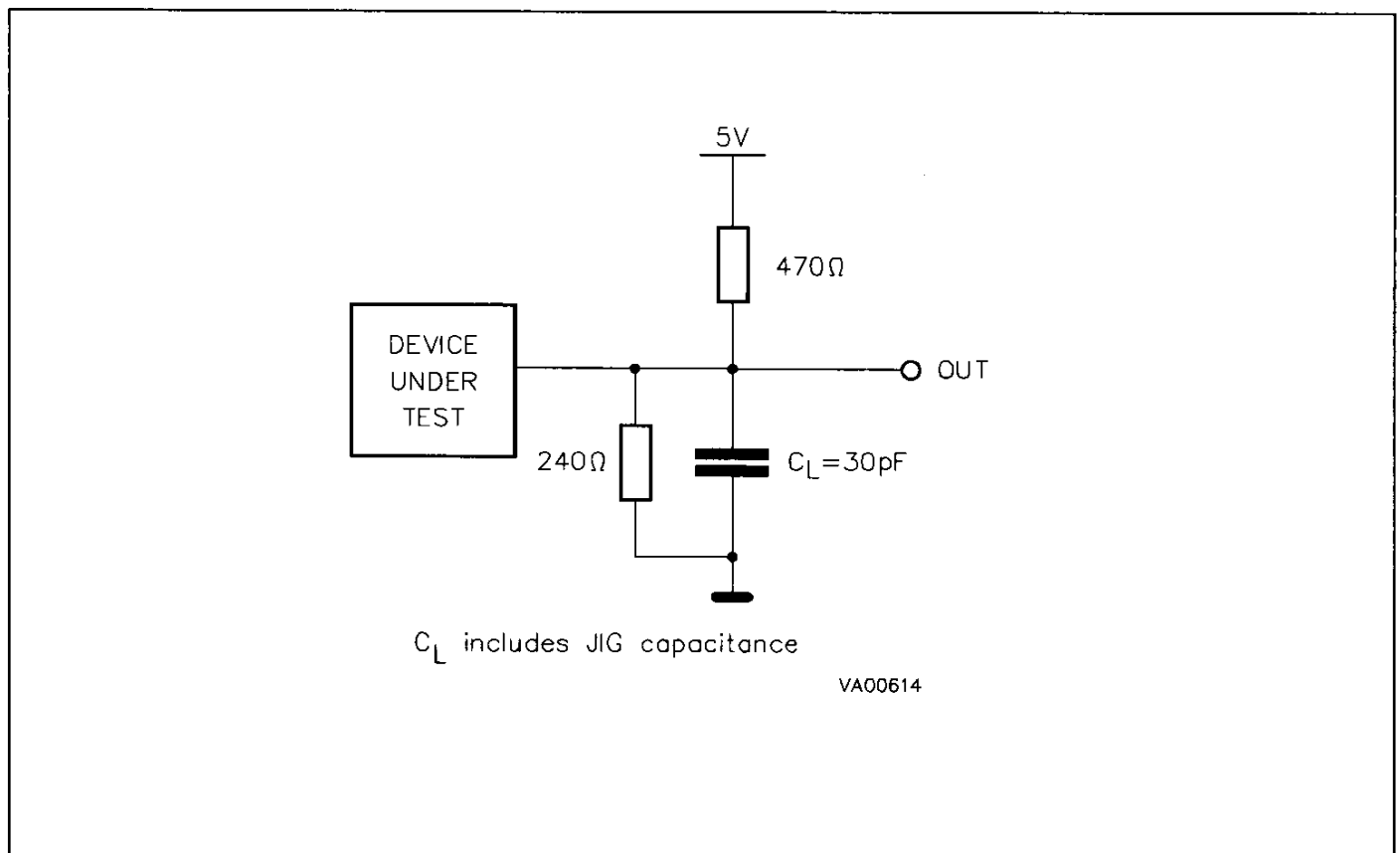
Symbol	Parameter	Typ.	Max.	Unit	Note
C <sub>1</sub>	Capacitance on Input Pins		8	pF	1
C <sub>0</sub>	Capacitance on Output Pins		12	pF	1,2

**Notes :** 1. This parameter is only sampled and not 100% tested  
 2. Output buffer deselected

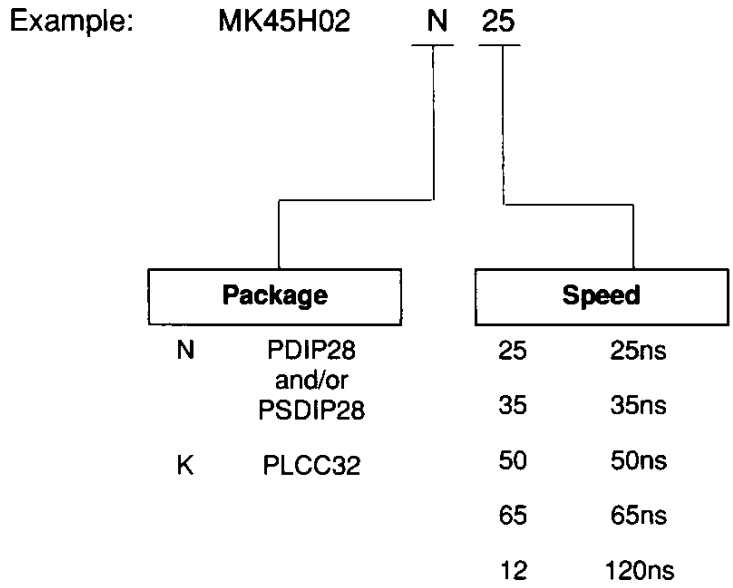
## AC TEST CONDITIONS

Parameter	Value	Unit
Input Levels	0 to 3	V
Transition Time	5	ns
Input Signal Timing Reference Level	1.5	V
Output Signal Timing Reference Levels	1.5 and 1.9	V
Ambient Temperature	0 to 70	°C
Supply Voltage	5 ±10%	V

Figure 17. Equivalent Output Load Circuit



**ORDERING INFORMATION**



For a list of available options of Package and Speed, refer to the Selector Guide in this Data Book or to the current Memory Shortform Catalogue.

For further information on any aspect of this device, please contact our Sales Office nearest you.